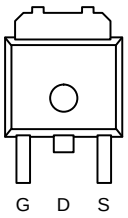
N-Channel 20-V (D-S), 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a, b]
20	0.006 @ V_{GS} = 4.5 V	30
	0.009 @ V_{GS} = 2.5 V	25

175°C Rated
Maximum Junction Temperature
TrenchFET®
Power MOSFETs

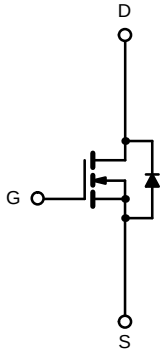
TO-252



Top View

Order Number:
SUD50N02-06

Drain Connected to Tab



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current[a, b]	T_A = 25°C	I_D	30	A
	T_A = 100°C		21	
Pulsed Drain Current		I_{DM}	100	
Continuous Source Current (Diode Conduction)[a, b]		I_S	30	
Maximum Power Dissipation	T_C = 25°C	P_D	100	W
	T_A = 25°C		8.3[a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 sec.	R_{thJA}	15	18	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	1.2	1.5	

Notes
a. Surface Mounted on 1" x 1" FR4 Board
b. t ≤ 10 sec.

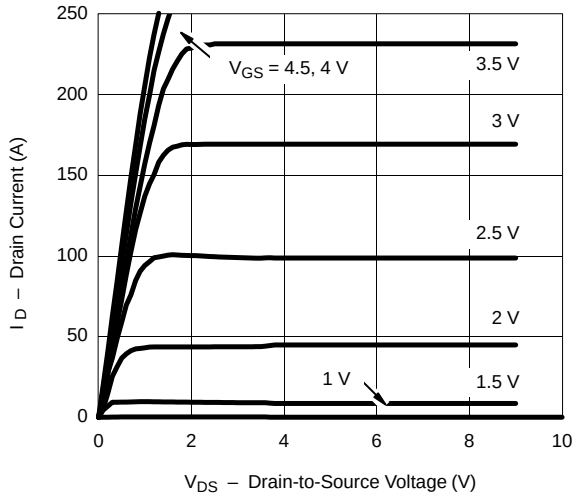
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.6			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 125°C			50	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	50			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 30 A			0.006	Ω
		V_{GS} = 4.5 V, I_D =30 A, T_J = 125°C			0.009	
		V_{GS} = 2.5 V, I_D = 20 A			0.009	
Forward Transconductance[b]	g_{fs}	V_{DS} = 5 V, I_D = 30 A	20			S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		6600		pF
Output Capacitance	C_{oss}			1150		
Reverse Transfer Capacitance	C_{rss}			600		
Total Gate Charge[c]	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 50 A		65	130	nC
Gate-Source Charge[c]	Q_{gs}			13		
Gate-Drain Charge[c]	Q_{gd}			14		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 10 V, R_L = 0.2 Ω I_D ≅ 50 A, V_{GEN} = 4.5 V, R_G = 2.5 Ω		25	40	ns
Rise Time[c]	t_r			120	180	
Turn-Off Delay Time[c]	$t_{d(off)}$			80	120	
Fall Time[c]	t_f			100	150	
Source-Drain Diode Ratings and Characteristic (T_C = 25°C)						
Pulsed Current	I_{SM}				100	A
Diode Forward Voltage[b]	V_{SD}	I_F = 100 A, V_{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 50 A, di/dt = 100 A/µs		45	100	ns

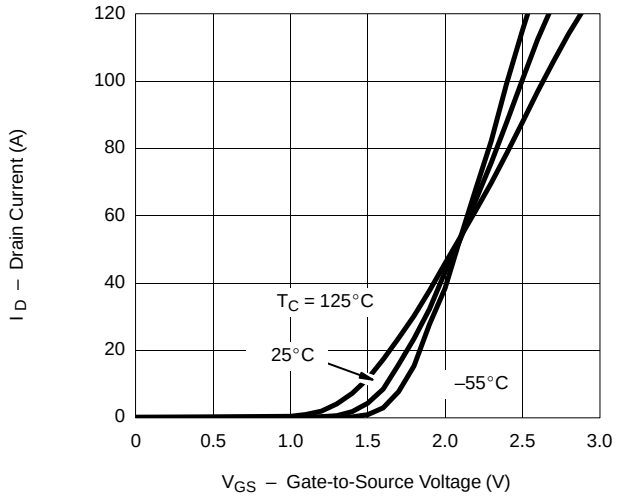
Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

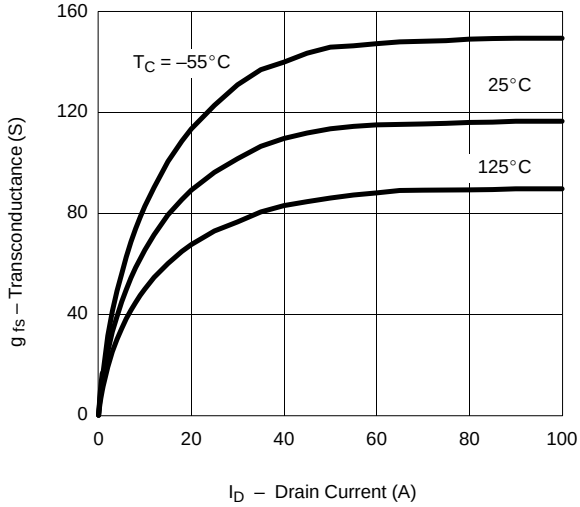
Output Characteristics



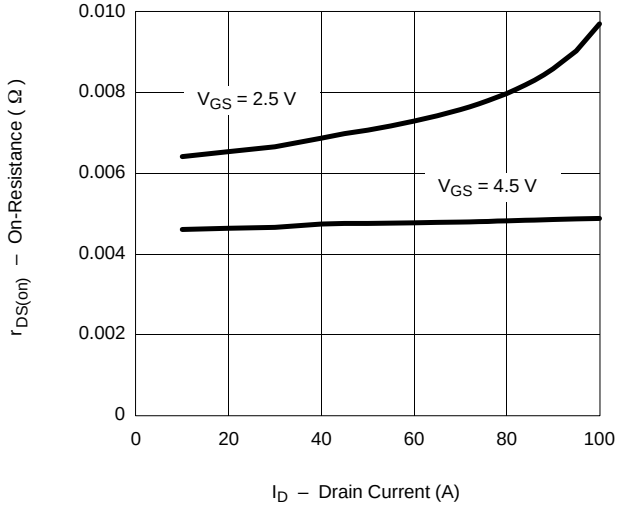
Transfer Characteristics



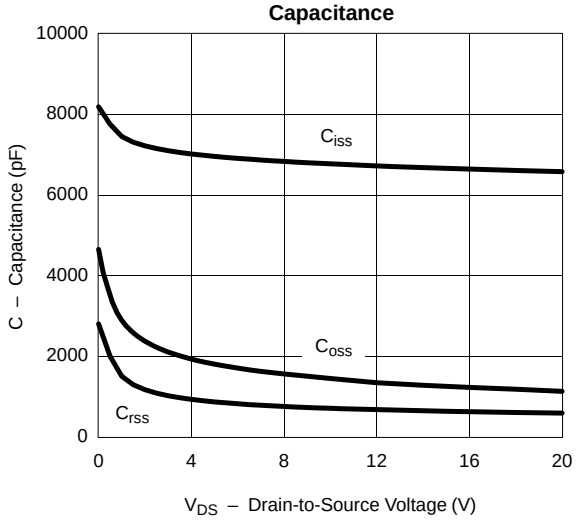
Transconductance



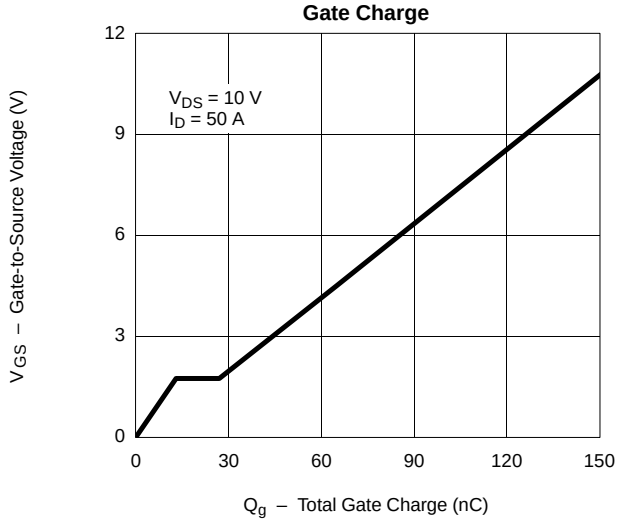
On-Resistance vs. Drain Current



Capacitance

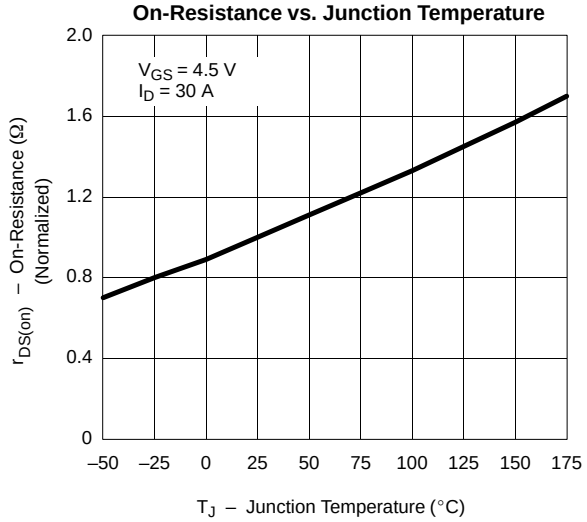


Gate Charge

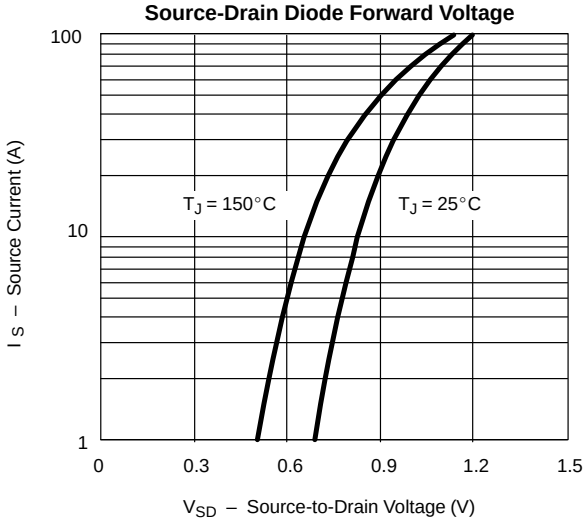


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

On-Resistance vs. Junction Temperature

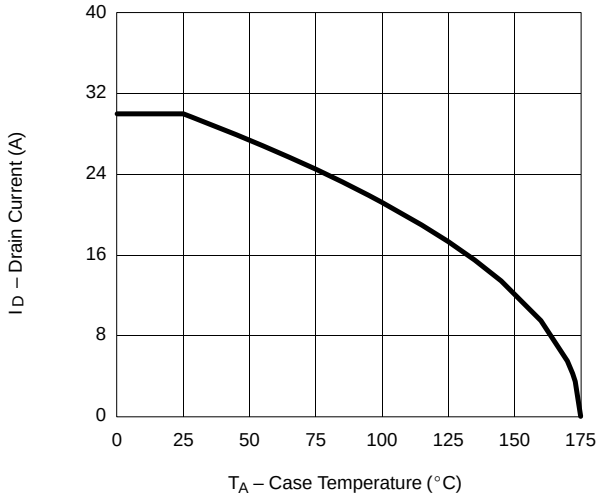


Source-Drain Diode Forward Voltage

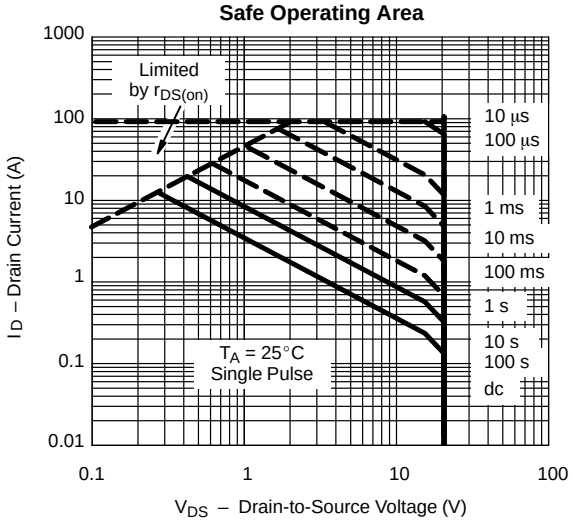


THERMAL RATINGS

Maximum Avalanche Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient